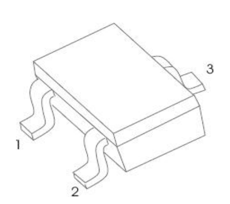
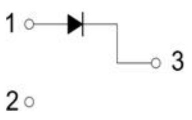
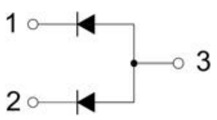
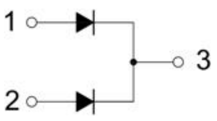
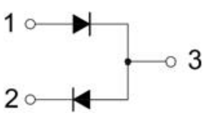
Plastic-Encapsulate Diode

SWITCHING DIODE



FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

MMBD4448HT	MMBD4448HTA	MMBD4448HTC	MMBD4448HTS
			
MARKING:A3	**MARKING:A6**	**MARKING:A7**	**MARKING:AB**

Maximum Ratings and Electrical Characteristics, Single Diode @T_a=25 ℃

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage **Working Peak Reverse Voltage** **DC Blocking Voltage**	V_{RRM} V_{RWM} V_R	80	V
RMS Reverse Voltage	$V_{R(RMS)}$	57	V
Forward Continuous Current	I_{FM}	500	mA
Average Rectified Output Current	I_O	250	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Power Dissipation	Pd	150	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	℃/W
Storage Temperature	T_{STG}	-55 ~+150	℃

Electrical Ratings @T_a=25℃

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	V_R	80			V	I_R=2.5 μA
Forward voltage	V_{F1}	0.62		0.72	V	I_F=5mA
	V_{F2}			0.855	V	I_F=10mA
	V_{F3}			1.0	V	I_F=100mA
	V_{F4}			1.25	V	I_F=150mA
Reverse current	I_{R1}			0.1	μA	V_R=70V
	I_{R2}			25	nA	V_R=20V
Capacitance between terminals	C_T			3.5	pF	V_R=6V,f=1MHz
Reverse recovery time	t_{rr}			4	ns	I_F=I_R=10mA Irr=0.1XI_R,R_L=100Ω

Typical Characteristics